What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	M16C/60
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, IEBus, UART/USART
Peripherals	DMA, WDT
Number of I/O	85
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 26x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-BQFP
Supplier Device Package	100-QFP (14x20)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/m3062lfgpfp-u3c

M16C/62P Group (M16C/62P, M16C/62PT)

SINGLE-CHIP 16-BIT CMOS MICROCOMPUTER

REJ03B0001-0241
Rev.2.41
Jan 10, 2006

1. Overview

The M16C/62P Group (M16C/62P, M16C/62PT) of single-chip microcomputers are built using the high performance silicon gate CMOS process using a M16C/60 Series CPU core and are packaged in a 80-pin, 100-pin and 128-pin plastic molded QFP. These single-chip microcomputers operate using sophisticated instructions featuring a high level of instruction efficiency. With 1M bytes of address space, they are capable of executing instructions at high speed. In addition, this microcomputer contains a multiplier and DMAC which combined with fast instruction processing capability, makes it suitable for control of various OA, communication, and industrial equipment which requires high-speed arithmetic/logic operations.

1.1 Applications

Audio, cameras, television, home appliance, office/communications/portable/industrial equipment, automobile, etc.

Specifications written in this manual are believed to be accurate, but are not guaranteed to be entirely free of error. Specifications in this manual may be changed for functional or performance improvements. Please make sure your manual is the latest edition.

1.2 Performance Outline

Table 1.1 to 1.3 list Performance Outline of M16C/62P Group (M16C/62P, M16C/62PT)(128-pin version).

Table 1.1 Performance Outline of M16C/62P Group (M16C/62P, M16C/62PT)(128-pin version)

	Item	Performance
		M16C/62P
CPU	Number of Basic Instructions	91 instructions
	Minimum Instruction Execution Time	41.7ns(f(BCLK)=24MHz, VCC1=3.3 to 5.5V) 100ns(f(BCLK)=10MHz, VCC1=2.7 to 5.5V)
	Operating Mode	Single-chip, memory expansion and microprocessor mode
	Address Space	1 Mbyte (Available to 4 Mbytes by memory space expansion function)
	Memory Capacity	See **Table 1.4 to 1.5 Product List**
Peripheral Function	Port	Input/Output : 113 pins, Input : 1 pin
	Multifunction Timer	Timer A : 16 bits x 5 channels, Timer B : 16 bits x 6 channels, Three phase motor control circuit
	Serial Interface	3 channels Clock synchronous, UART, I^2C bus(1), IEBus(2) 2 channels Clock synchronous
	A/D Converter	10-bit A/D converter: 1 circuit, 26 channels
	D/A Converter	8 bits x 2 channels
	DMAC	2 channels
	CRC Calculation Circuit	CCITT-CRC
	Watchdog Timer	15 bits x 1 channel (with prescaler)
	Interrupt	Internal: 29 sources, External: 8 sources, Software: 4 sources, Priority level: 7 levels
	Clock Generation Circuit	4 circuits Main clock generation circuit (*), Subclock generation circuit (*), On-chip oscillator, PLL synthesizer (*)Equipped with a built-in feedback resistor.
	Oscillation Stop Detection Function	Stop detection of main clock oscillation, re-oscillation detection function
	Voltage Detection Circuit	Available (option(4))
Electric Characteristics	Supply Voltage	VCC1=3.0 to 5.5 V, VCC2=2.7V to VCC1 (f(BCLK=24MHz) VCC1=2.7 to 5.5 V, VCC2=2.7V to VCC1 (f(BCLK=10MHz)
	Power Consumption	14 mA (VCC1=VCC2=5V, f(BCLK)=24MHz) 8 mA (VCC1=VCC2=3V, f(BCLK)=10MHz) 1.8μA (VCC1=VCC2=3V, f(XCIN)=32kHz, wait mode) 0.7μA (VCC1=VCC2=3V, stop mode)
Flash memory version	Program/Erase Supply Voltage	3.3±0.3 V or 5.0±0.5 V
	Program and Erase Endurance	100 times (all area) or 1,000 times (user ROM area without block A and block 1) / 10,000 times (block A, block 1) (3)
Operating Ambient Temperature		-20 to 85°C, -40 to 85°C (3)
Package		128-pin plastic mold LQFP

NOTES:

1. I^2C bus is a registered trademark of Koninklijke Philips Electronics N. V.
2. IEBus is a registered trademark of NEC Electronics Corporation.
3. See **Table 1.8 Product Code** for the program and erase endurance, and operating ambient temperature. In addition 1,000 times/10,000 times are under development as of Jul., 2005. Please inquire about a release schedule.
4. All options are on request basis.

Table 1.7 Product List (4) (V version (M16C/62PT)) As of Dec. 2005

Type No.	ROM Capacity	RAM Capacity	Package Type(1)	Remarks	
M3062CM6V-XXXFP (P)	48 Kbytes	4 Kbytes	PRQP0100JB-A	Mask ROM version	V Version (High reliability 125°C version)
M3062CM6V-XXXGP (P)			PLQP0100KB-A		
M3062EM6V-XXXGP (P)			PRQP0080JA-A		
M3062CM8V-XXXFP (P)	64 Kbytes	4 Kbytes	PRQP0100JB-A		
M3062CM8V-XXXGP (P)			PLQP0100KB-A		
M3062EM8V-XXXGP (P)			PRQP0080JA-A		
M3062CMAV-XXXFP (P)	96 Kbytes	5 Kbytes	PRQP0100JB-A		
M3062CMAV-XXXGP (P)			PLQP0100KB-A		
M3062EMAV-XXXGP (P)			PRQP0080JA-A		
M3062AMCV-XXXFP (D)	128 Kbytes	10 Kbytes	PRQP0100JB-A		
M3062AMCV-XXXGP (D)			PLQP0100KB-A		
M3062BMCV-XXXGP (P)			PRQP0080JA-A		
M3062AFCVFP (D)	128K+4 Kbytes	10 Kbytes	PRQP0100JB-A	Flash memory version (2)	
M3062AFCVGP (D)			PLQP0100KB-A		
M3062BFCVGP (P)			PRQP0080JA-A		
M3062JFHVFP (P)	384K+4 Kbytes	31 Kbytes	PRQP0100JB-A		
M3062JFHVGP (P)			PLQP0100KB-A		

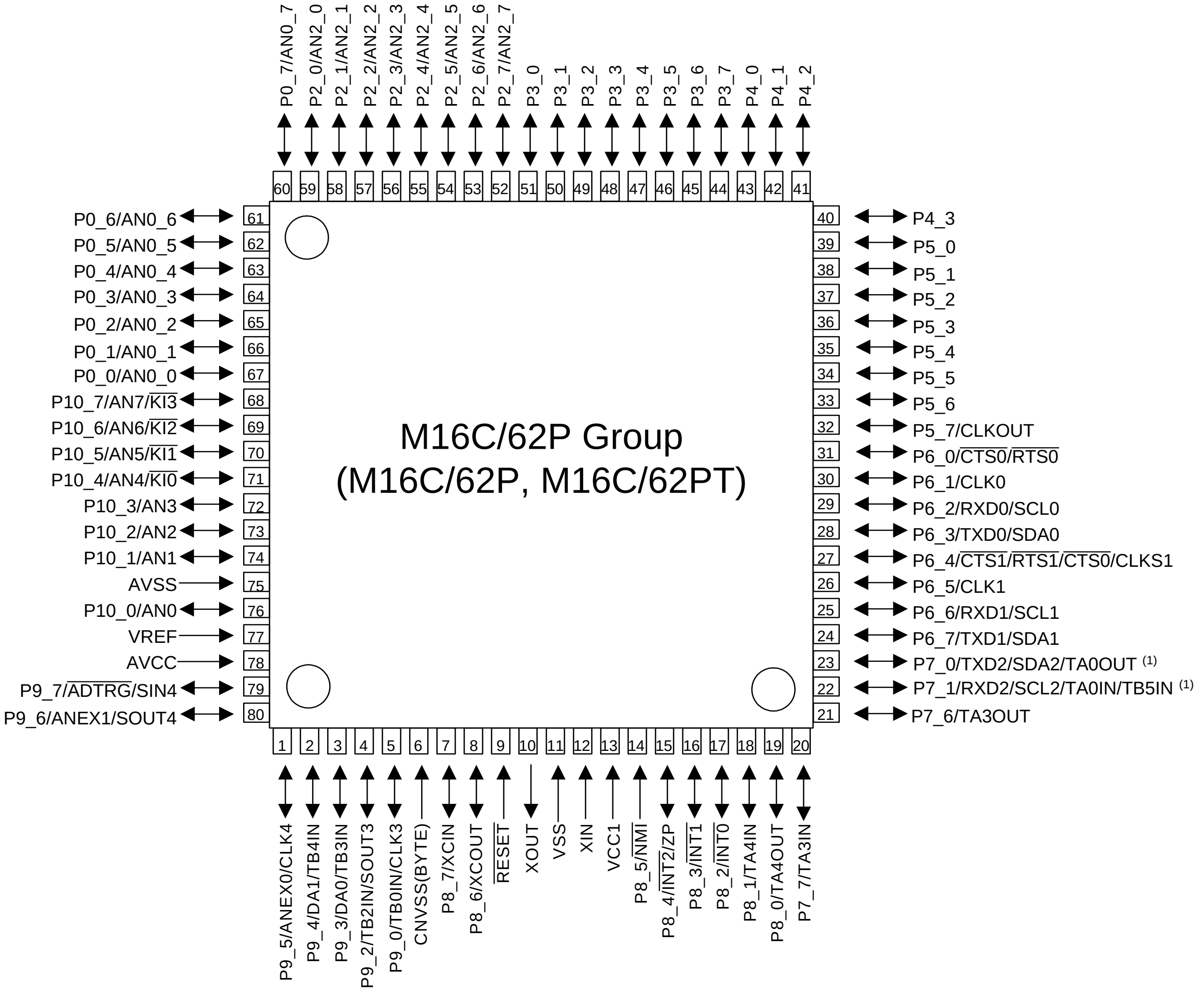
(D): Under development
(P): Under planning
NOTES:

1. The old package type numbers of each package type are as follows.
   PLQP0128KB-A : 128P6Q-A,
   PRQP0100JB-A : 100P6S-A,
   PLQP0100KB-A : 100P6Q-A,
   PRQP0080JA-A : 80P6S-A
2. In the flash memory version, there is 4K bytes area (block A).

Table 1.14 Pin Characteristics for 100-Pin Package (2)

Pin No.		Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
FP	GP							
51	49		P4_3					A19
52	50		P4_2					A18
53	51		P4_1					A17
54	52		P4_0					A16
55	53		P3_7					A15
56	54		P3_6					A14
57	55		P3_5					A13
58	56		P3_4					A12
59	57		P3_3					A11
60	58		P3_2					A10
61	59		P3_1					A9
62	60	VCC2						
63	61		P3_0					A8(/-/D7)
64	62	VSS						
65	63		P2_7				AN2_7	A7(/D7/D6)
66	64		P2_6				AN2_6	A6(/D6/D5)
67	65		P2_5				AN2_5	A5(/D5/D4)
68	66		P2_4				AN2_4	A4(/D4/D3)
69	67		P2_3				AN2_3	A3(/D3/D2)
70	68		P2_2				AN2_2	A2(/D2/D1)
71	69		P2_1				AN2_1	A1(/D1/D0)
72	70		P2_0				AN2_0	A0(/D0/-)
73	71		P1_7	$\overline{\text{INT5}}$				D15
74	72		P1_6	$\overline{\text{INT4}}$				D14
75	73		P1_5	$\overline{\text{INT3}}$				D13
76	74		P1_4					D12
77	75		P1_3					D11
78	76		P1_2					D10
79	77		P1_1					D9
80	78		P1_0					D8
81	79		P0_7				AN0_7	D7
82	80		P0_6				AN0_6	D6
83	81		P0_5				AN0_5	D5
84	82		P0_4				AN0_4	D4
85	83		P0_3				AN0_3	D3
86	84		P0_2				AN0_2	D2
87	85		P0_1				AN0_1	D1
88	86		P0_0				AN0_0	D0
89	87		P10_7	$\overline{\text{KI3}}$			AN7	
90	88		P10_6	$\overline{\text{KI2}}$			AN6	
91	89		P10_5	$\overline{\text{KI1}}$			AN5	
92	90		P10_4	$\overline{\text{KI0}}$			AN4	
93	91		P10_3				AN3	
94	92		P10_2				AN2	
95	93		P10_1				AN1	
96	94	AVSS						
97	95		P10_0				AN0	
98	96	VREF						
99	97	AVCC						
100	98		P9_7			SIN4	$\overline{\text{ADTRG}}$	

PIN CONFIGURATION (top view)



NOTES:
1. P7_0 and P7_1 are N channel open-drain output pins.

Package : PRQP0080JA-A (80P6S-A)

Figure 1.9 Pin Configuration (Top View)

Table 4.5 SFR Information (5) (1)

Address	Register	Symbol	After Reset
0380h	Count Start Flag	TABSR	00h
0381h	Clock Prescaler Reset Fag	CPSRF	0XXXXXXXb
0382h	One-Shot Start Flag	ONSF	00h
0383h	Trigger Select Register	TRGSR	00h
0384h	Up-Down Flag	UDF	00h (2)
0385h			
0386h 0387h	Timer A0 Register	TA0	XXh XXh
0388h 0389h	Timer A1 Register	TA1	XXh XXh
038Ah 038Bh	Timer A2 Register	TA2	XXh XXh
038Ch 038Dh	Timer A3 Register	TA3	XXh XXh
038Eh 038Fh	Timer A4 Register	TA4	XXh XXh
0390h 0391h	Timer B0 Register	TB0	XXh XXh
0392h 0393h	Timer B1 Register	TB1	XXh XXh
0394h 0395h	Timer B2 Register	TB2	XXh XXh
0396h	Timer A0 Mode Register	TA0MR	00h
0397h	Timer A1 Mode Register	TA1MR	00h
0398h	Timer A2 Mode Register	TA2MR	00h
0399h	Timer A3 Mode Register	TA3MR	00h
039Ah	Timer A4 Mode Register	TA4MR	00h
039Bh	Timer B0 Mode Register	TB0MR	00XX0000b
039Ch	Timer B1 Mode Register	TB1MR	00XX0000b
039Dh	Timer B2 Mode Register	TB2MR	00XX0000b
039Eh	Timer B2 Special Mode Register	TB2SC	XXXXXX00b
039Fh			
03A0h	UART0 Transmit/Receive Mode Register	U0MR	00h
03A1h	UART0 Bit Rate Generator	U0BRG	XXh
03A2h 03A3h	UART0 Transmit Buffer Register	U0TB	XXh XXh
03A4h	UART0 Transmit/Receive Control Register 0	U0C0	00001000b
03A5h	UART0 Transmit/Receive Control Register 1	U0C1	00XX0010b
03A6h 03A7h	UART0 Receive Buffer Register	U0RB	XXh XXh
03A8h	UART1 Transmit/Receive Mode Register	U1MR	00h
03A9h	UART1 Bit Rate Generator	U1BRG	XXh
03AAh 03ABh	UART1 Transmit Buffer Register	U1TB	XXh XXh
03ACh	UART1 Transmit/Receive Control Register 0	U1C0	00001000b
03ADh	UART1 Transmit/Receive Control Register 1	U1C1	00XX0010b
03AEh 03AFh	UART1 Receive Buffer Register	U1RB	XXh XXh
03B0h	UART Transmit/Receive Control Register 2	UCON	X0000000b
03B1h			
03B2h			
03B3h			
03B4h			
03B5h			
03B6h			
03B7h			
03B8h	DMA0 Request Factor Select Register	DM0SL	00h
03B9h			
03BAh	DMA1 Request Factor Select Register	DM1SL	00h
03BBh			
03BCh 03BDh	CRC Data Register	CRCD	XXh XXh
03BEh	CRC Input Register	CRCIN	XXh
03BFh			

NOTES:

1. The blank areas are reserved and cannot be accessed by users.
2. Bit 5 in the Up-down flag is “0” by reset. However, The values in these bits when read are indeterminate.

X : Nothing is mapped to this bit

Table 5.6 Flash Memory Version Electrical Characteristics (1) for 100 cycle products (D3, D5, U3, U5)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3)		100			cycle
–	Word Program Time (V_{CC1}=5.0V)			25	200	µs
–	Lock Bit Program Time			25	200	µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block		0.3	4	s
–		8-Kbyte block		0.3	4	s
–		32-Kbyte block		0.5	4	s
–		64-Kbyte block		0.8	4	s
–	Erase All Unlocked Blocks Time (2)				4×n	s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		10			year

Table 5.7 Flash Memory Version Electrical Characteristics (6) for 10,000 cycle products (D7, D9, U7, U9) (Block A and Block 1 (7))

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3, 8, 9)		10,000 (4)			cycle
–	Word Program Time (V_{CC1}=5.0V)			25		µs
–	Lock Bit Program Time			25		µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block		0.3		s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		10			year

NOTES:

1. Referenced to V_{CC1}=4.5 to 5.5V, 3.0 to 3.6V at Topr = 0 to 60 °C (D3, D5, U3, U5) unless otherwise specified.
2. n denotes the number of block erases.
3. Program and Erase Endurance refers to the number of times a block erase can be performed.
   If the program and erase endurance is n (n=100, 1,000, or 10,000), each block can be erased n times.
   For example, if a 4 Kbytes block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one program and erase endurance. Data cannot be written to the same address more than once without erasing the block. (Rewrite prohibited)
4. Maximum number of E/W cycles for which operation is guaranteed.
5. Topr = -40 to 85 °C (D3, D7, U3, U7) / -20 to 85 °C (D5, D9, U5, U9).
6. Referenced to V_{CC1} = 4.5 to 5.5V, 3.0 to 3.6V at T_{opr} = -40 to 85 °C (D7, U7) / -20 to 85 °C (D9, U9) unless otherwise specified.
7. Table 5.7 applies for block A or block 1 program and erase endurance > 1,000. Otherwise, use Table 5.6.
8. To reduce the number of program and erase endurance when working with systems requiring numerous rewrites, write to unused word addresses within the block instead of rewrite. Erase block only after all possible addresses are used. For example, an 8-word program can be written 256 times maximum before erase becomes necessary.
   Maintaining an equal number of erasure between block A and block 1 will also improve efficiency. It is important to track the total number of times erasure is used.
9. Should erase error occur during block erase, attempt to execute clear status register command, then block erase command at least three times until erase error disappears.
10. Set the PM17 bit in the PM1 register to “1” (wait state) when executing more than 100 times rewrites (D7, D9, U7 and U9).
11. Customers desiring E/W failure rate information should contact their Renesas technical support representative.

Table 5.8 Flash Memory Version Program / Erase Voltage and Read Operation Voltage Characteristics (at T_{opr} = 0 to 60 °C(D3, D5, U3, U5), T_{opr} = -40 to 85 °C(D7, U7) / T_{opr} = -20 to 85 °C(D9, U9))

Flash Program, Erase Voltage	Flash Read Operation Voltage
V_{CC1} = 3.3 V ± 0.3 V or 5.0 V ± 0.5 V	V_{CC1}=2.7 to 5.5 V

Table 5.9 Low Voltage Detection Circuit Electrical Characteristics

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det4}	Low Voltage Detection Voltage (1)	V_{CC1}=0.8V to 5.5V	3.3	3.8	4.4	V
V_{det3}	Reset Level Detection Voltage (1, 2)		2.2	2.8	3.6	V
V_{det4}-V_{det3}	Electric potential difference of Low Voltage Detection and Reset Level Detection		0.3			V
V_{det3s}	Low Voltage Reset Retention Voltage				0.8	V
V_{det3r}	Low Voltage Reset Release Voltage (3)		2.2	2.9	4.0	V

NOTES:

1. V_{det4} > V_{det3}.
2. Where reset level detection voltage is less than 2.7 V, if the supply power voltage is greater than the reset level detection voltage, the microcomputer operates with f(BCLK) ≤ 10MHz.
3. V_{det3r} > V_{det3} is not guaranteed.
4. The voltage detection circuit is designed to use when VCC1 is set to 5V.

Table 5.10 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for Internal Power Supply Stabilization During Powering-On	V_{CC1}=2.7V to 5.5V			2	ms
$t_{d(R-S)}$	STOP Release Time				150	µs
$t_{d(W-S)}$	Low Power Dissipation Mode Wait Mode Release Time				150	µs
$t_{d(S-R)}$	Brown-out Detection Reset (Hardware Reset 2) Release Wait Time	V_{CC1}=V_{det3r} to 5.5V		6 (1)	20	ms
$t_{d(E-A)}$	Low Voltage Detection Circuit Operation Start Time	V_{CC1}=2.7V to 5.5V			20	µs

NOTES:

1. When V_{CC1} = 5V.

$V_{CC1}=V_{CC2}=5V$

Table 5.11 Electrical Characteristics (1) (1)

Symbol	Parameter			Measuring Condition	Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	HIGH Output Voltage (3)	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1		$I_{OH}=-5mA$	$V_{CC1}-2.0$		V_{CC1}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		$I_{OH}=-5mA$ (2)	$V_{CC2}-2.0$		V_{CC2}	
V_{OH}	HIGH Output Voltage (3)	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1		$_{OH}=-200\mu A$	$V_{CC1}-0.3$		V_{CC1}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		$I_{OH}=-200\mu A$ (2)	$V_{CC2}-0.3$		V_{CC2}	
V_{OH}	HIGH Output Voltage XOUT		HIGHPOWER	$I_{OH}=-1mA$	$V_{CC1}-2.0$		V_{CC1}	V
			LOWPOWER	$I_{OH}=-0.5mA$	$V_{CC1}-2.0$		V_{CC1}	
	HIGH Output Voltage XCOUT		HIGHPOWER	With no load applied		2.5		V
			LOWPOWER	With no load applied		1.6		
V_{OL}	LOW Output Voltage (3)	P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1		$I_{OL}=5mA$			2.0	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		$I_{OL}=5mA$ (2)			2.0	
V_{OL}	LOW Output Voltage (3)	P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1		$I_{OL}=200\mu A$			0.45	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		$I_{OL}=200\mu A$ (2)			0.45	
V_{OL}	LOW Output Voltage XOUT		HIGHPOWER	$I_{OL}=1mA$			2.0	V
			LOWPOWER	$I_{OL}=0.5mA$			2.0	
	LOW Output Voltage XCOUT		HIGHPOWER	With no load applied		0		V
			LOWPOWER	With no load applied		0		
$V_{T+}-V_{T-}$	Hysteresis	$\overline{\mathrm{HOLD}}$, $\overline{\mathrm{RDY}}$, TA0IN to TA4IN, TB0IN to TB5IN, $\overline{\mathrm{INT0}}$ to $\overline{\mathrm{INT5}}$, $\overline{\mathrm{NMI}}$, $\overline{\mathrm{ADTRG}}$, $\overline{\mathrm{CTS0}}$ to $\overline{\mathrm{CTS2}}$, CLK0 to CLK4, TA0OUT to TA4OUT, $\overline{\mathrm{KI0}}$ to $\overline{\mathrm{KI3}}$, RXD0 to RXD2, SCL0 to SCL2, SDA0 to SDA2, SIN3, SIN4			0.2		1.0	V
$V_{T+}-V_{T-}$	Hysteresis	$\overline{\mathrm{RESET}}$			0.2		2.5	V
I_{IH}	HIGH Input Current (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1, XIN, $\overline{\mathrm{RESET}}$, CNVSS, BYTE		$V_I=5V$			5.0	μA
I_{IL}	LOW Input Current (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7,P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1, XIN, $\overline{\mathrm{RESET}}$, CNVSS, BYTE		$V_I=0V$			−5.0	μA
R_{PULLUP}	Pull-Up Resistance (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7,P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1		$V_I=0V$	30	50	170	kΩ
R_{fXIN}	Feedback Resistance XIN					1.5		MΩ
R_{fXCIN}	Feedback Resistance XCIN					15		MΩ
V_{RAM}	RAM Retention Voltage			At stop mode	2.0			V

NOTES:

1. Referenced to $V_{CC1}=V_{CC2}=4.2$ to 5.5V, V_{SS} = 0V at T_{opr} = −20 to 85°C / −40 to 85°C, f(BCLK)=24MHz unless otherwise specified.
2. Where the product is used at V_{CC1} = 5 V and V_{CC2} = 3 V, refer to the 3 V version value for the pin specified value on V_{CC2} port side.
3. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.

$V_{CC1}=V_{CC2}=5V$

Timing Requirements
(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.13 External Clock Input (XIN input) (1)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
t_c	External Clock Input Cycle Time	62.5		ns
$t_{w(H)}$	External Clock Input HIGH Pulse Width	25		ns
$t_{w(L)}$	External Clock Input LOW Pulse Width	25		ns
t_r	External Clock Rise Time		15	ns
t_f	External Clock Fall Time		15	ns

NOTES:

1. The condition is $V_{CC1}=V_{CC2}$=3.0 to 5.0V.

Table 5.14 Memory Expansion Mode and Microprocessor Mode

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{ac1(RD-DB)}$	Data Input Access Time (for setting with no wait)		(NOTE 1)	ns
$t_{ac2(RD-DB)}$	Data Input Access Time (for setting with wait)		(NOTE 2)	ns
$t_{ac3(RD-DB)}$	Data Input Access Time (when accessing multiplex bus area)		(NOTE 3)	ns
$t_{su(DB-RD)}$	Data Input Setup Time	40		ns
$t_{su(RDY-BCLK)}$	$\overline{\text{RDY}}$ Input Setup Time	30		ns
$t_{su(HOLD-BCLK)}$	$\overline{\text{HOLD}}$ Input Setup Time	40		ns
$t_{h(RD-DB)}$	Data Input Hold Time	0		ns
$t_{h(BCLK-RDY)}$	$\overline{\text{RDY}}$ Input Hold Time	0		ns
$t_{h(BCLK-HOLD)}$	$\overline{\text{HOLD}}$ Input Hold Time	0		ns

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 45[ns]$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{(n - 0.5) \times 10^9}{f(BCLK)} - 45[ns]$$

n is "2" for 1-wait setting, "3" for 2-wait setting and "4" for 3-wait setting.

3. Calculated according to the BCLK frequency as follows:

$$\frac{(n - 0.5) \times 10^9}{f(BCLK)} - 45[ns]$$

n is "2" for 2-wait setting, "3" for 3-wait setting.

Switching Characteristics
($V_{CC1} = V_{CC2} = 5V$, $V_{SS} = 0V$, at $T_{opr} = –20$ to 85°C / –40 to 85°C unless otherwise specified)

Table 5.27 Memory Expansion and Microprocessor Modes (for setting with no wait)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address Output Delay Time	See **Figure 5.2**		25	ns
$t_{h(BCLK-AD)}$	Address Output Hold Time (in relation to BCLK)		4		ns
$t_{h(RD-AD)}$	Address Output Hold Time (in relation to RD)		0		ns
$t_{h(WR-AD)}$	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
$t_{d(BCLK-CS)}$	Chip Select Output Delay Time			25	ns
$t_{h(BCLK-CS)}$	Chip Select Output Hold Time (in relation to BCLK)		4		ns
$t_{d(BCLK-ALE)}$	ALE Signal Output Delay Time			15	ns
$t_{h(BCLK-ALE)}$	ALE Signal Output Hold Time		–4		ns
$t_{d(BCLK-RD)}$	RD Signal Output Delay Time			25	ns
$t_{h(BCLK-RD)}$	RD Signal Output Hold Time		0		ns
$t_{d(BCLK-WR)}$	WR Signal Output Delay Time			25	ns
$t_{h(BCLK-WR)}$	WR Signal Output Hold Time		0		ns
$t_{d(BCLK-DB)}$	Data Output Delay Time (in relation to BCLK)			40	ns
$t_{h(BCLK-DB)}$	Data Output Hold Time (in relation to BCLK) (3)		4		ns
$t_{d(DB-WR)}$	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR) (3)		(NOTE 2)		ns
$t_{d(BCLK-HLDA)}$	HLDA Output Delay Time			40	ns

NOTES:

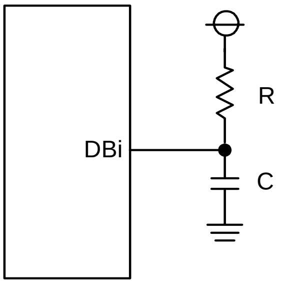
1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^9}{f(BCLK)} - 40[ns] \qquad f(BCLK) \text{ is 12.5MHz or less.}$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^9}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
Hold time of data bus is expressed in
$t = –CR \times \ln (1–V_{OL} / V_{CC2})$
by a circuit of the right figure.
For example, when $V_{OL} = 0.2V_{CC2}$, C = 30pF, R = 1kΩ, hold time of output "L" level is
$t = –30pF \times 1k\Omega \times \ln(1–0.2V_{CC2} / V_{CC2})$
$= 6.7ns.$



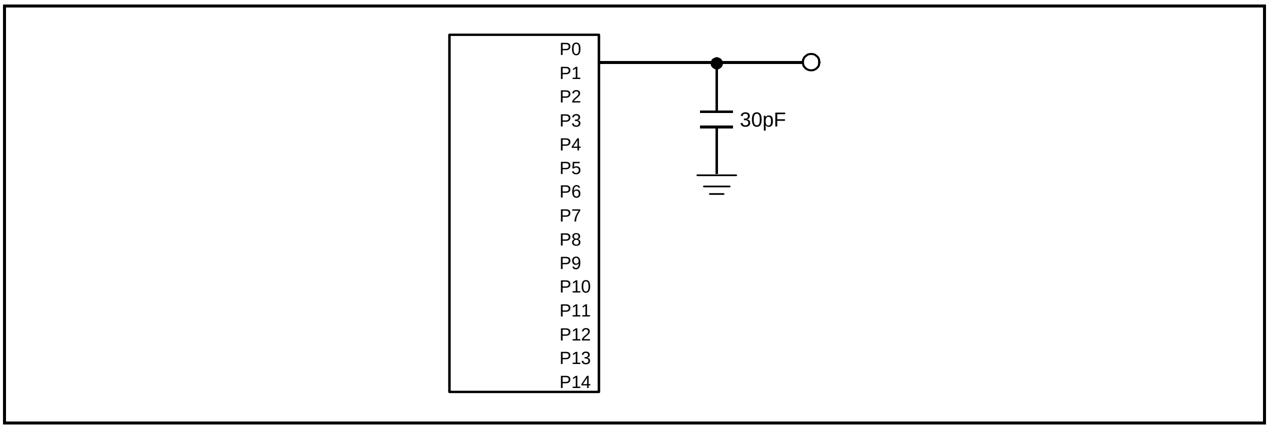


Figure 5.2 Ports P0 to P14 Measurement Circuit

VCC1=VCC2=5V

Switching Characteristics
(VCC1 = VCC2 = 5V, VSS = 0V, at Topr = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.29 Memory Expansion and Microprocessor Modes (for 2- to 3-wait setting, external area access and multiplex bus selection)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address Output Delay Time	See **Figure 5.2**		25	ns
$t_{h(BCLK-AD)}$	Address Output Hold Time (in relation to BCLK)		4		ns
$t_{h(RD-AD)}$	Address Output Hold Time (in relation to RD)		(NOTE 1)		ns
$t_{h(WR-AD)}$	Address Output Hold Time (in relation to WR)		(NOTE 1)		ns
$t_{d(BCLK-CS)}$	Chip Select Output Delay Time			25	ns
$t_{h(BCLK-CS)}$	Chip Select Output Hold Time (in relation to BCLK)		4		ns
$t_{h(RD-CS)}$	Chip Select Output Hold Time (in relation to RD)		(NOTE 1)		ns
$t_{h(WR-CS)}$	Chip Select Output Hold Time (in relation to WR)		(NOTE 1)		ns
$t_{d(BCLK-RD)}$	RD Signal Output Delay Time			25	ns
$t_{h(BCLK-RD)}$	RD Signal Output Hold Time		0		ns
$t_{d(BCLK-WR)}$	WR Signal Output Delay Time			25	ns
$t_{h(BCLK-WR)}$	WR Signal Output Hold Time		0		ns
$t_{d(BCLK-DB)}$	Data Output Delay Time (in relation to BCLK)			40	ns
$t_{h(BCLK-DB)}$	Data Output Hold Time (in relation to BCLK)		4		ns
$t_{d(DB-WR)}$	Data Output Delay Time (in relation to WR)		(NOTE 2)		ns
$t_{h(WR-DB)}$	Data Output Hold Time (in relation to WR)		(NOTE 1)		ns
$t_{d(BCLK-HLDA)}$	HLDA Output Delay Time			40	ns
$t_{d(BCLK-ALE)}$	ALE Signal Output Delay Time (in relation to BCLK)			15	ns
$t_{h(BCLK-ALE)}$	ALE Signal Output Hold Time (in relation to BCLK)		–4		ns
$t_{d(AD-ALE)}$	ALE Signal Output Delay Time (in relation to Address)		(NOTE 3)		ns
$t_{h(AD-ALE)}$	ALE Signal Output Hold Time (in relation to Address)		(NOTE 4)		ns
$t_{d(AD-RD)}$	RD Signal Output Delay From the End of Address		0		ns
$t_{d(AD-WR)}$	WR Signal Output Delay From the End of Address		0		ns
$t_{dz(RD-AD)}$	Address Output Floating Start Time			8	ns

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^9}{f(BCLK)} - 10[ns]$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{(n-0.5)\times10^9}{f(BCLK)} - 40[ns]$$

n is “2” for 2-wait setting, “3” for 3-wait setting.

3. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^9}{f(BCLK)} - 25[ns]$$

4. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^9}{f(BCLK)} - 15[ns]$$

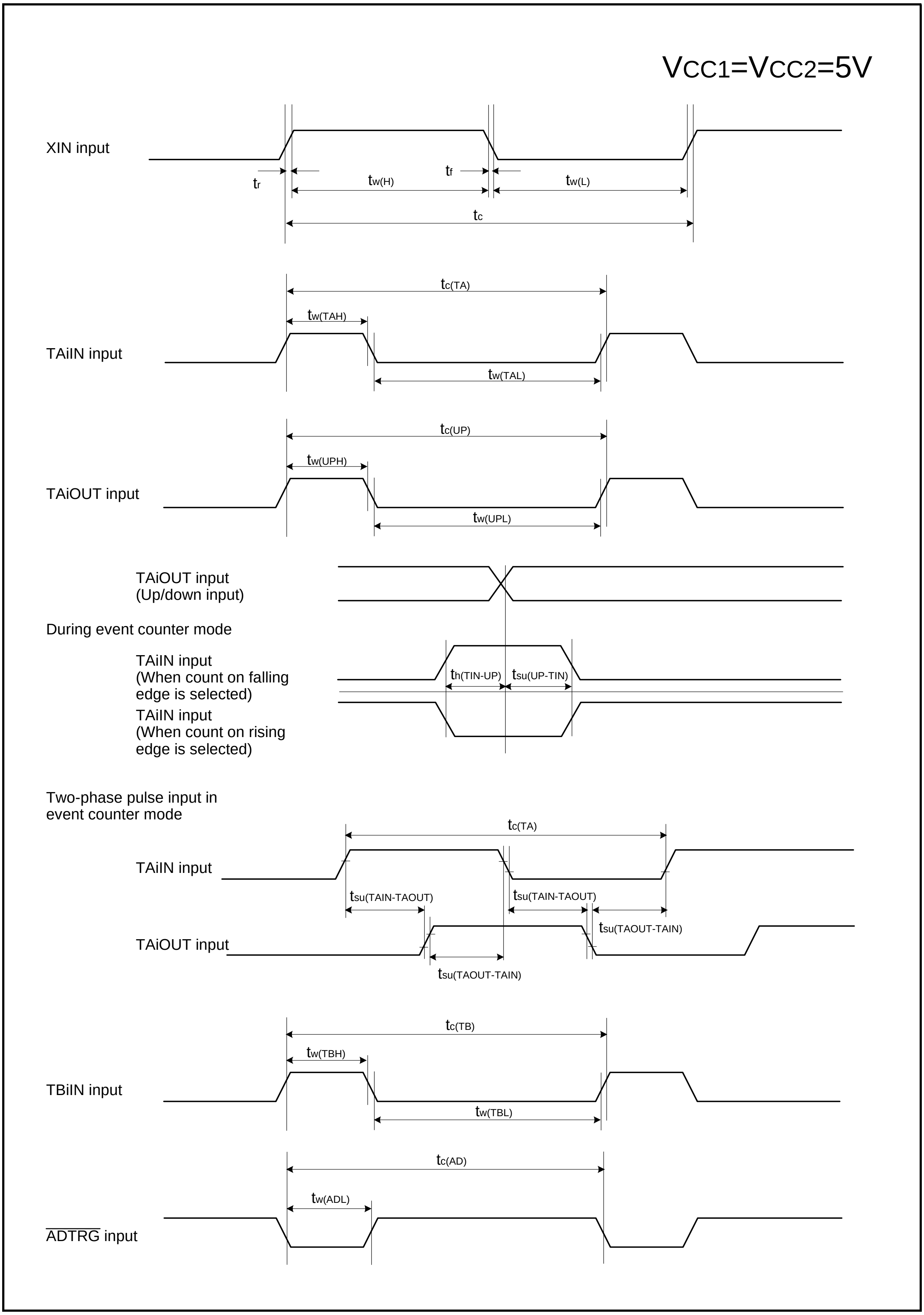


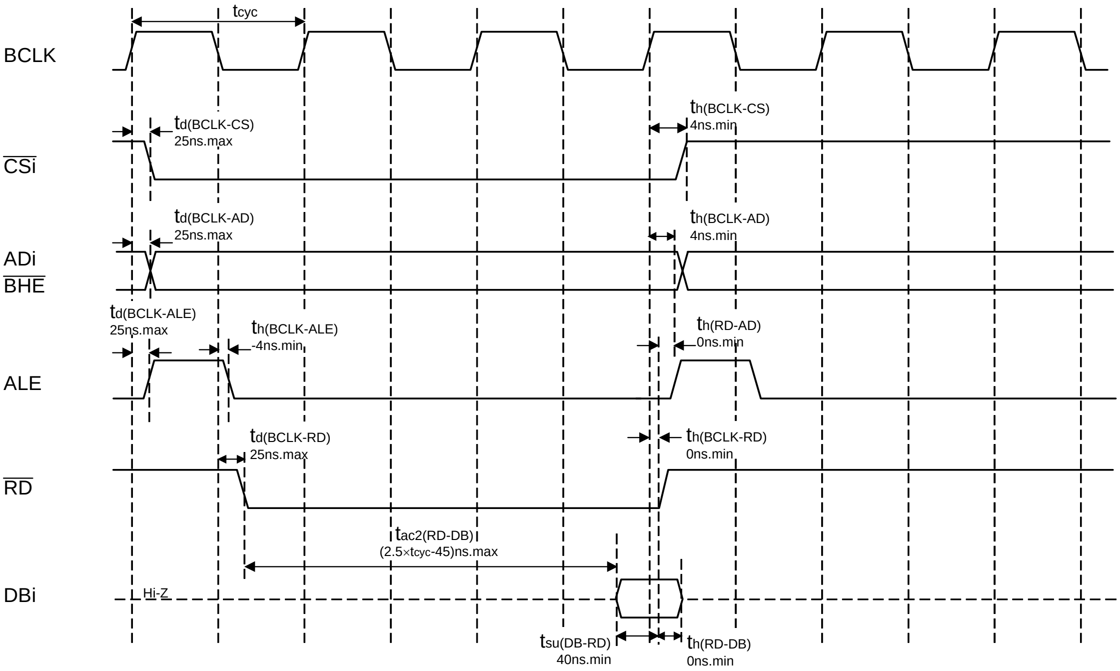
Figure 5.3 Timing Diagram (1)

$V_{CC1}=V_{CC2}=5V$

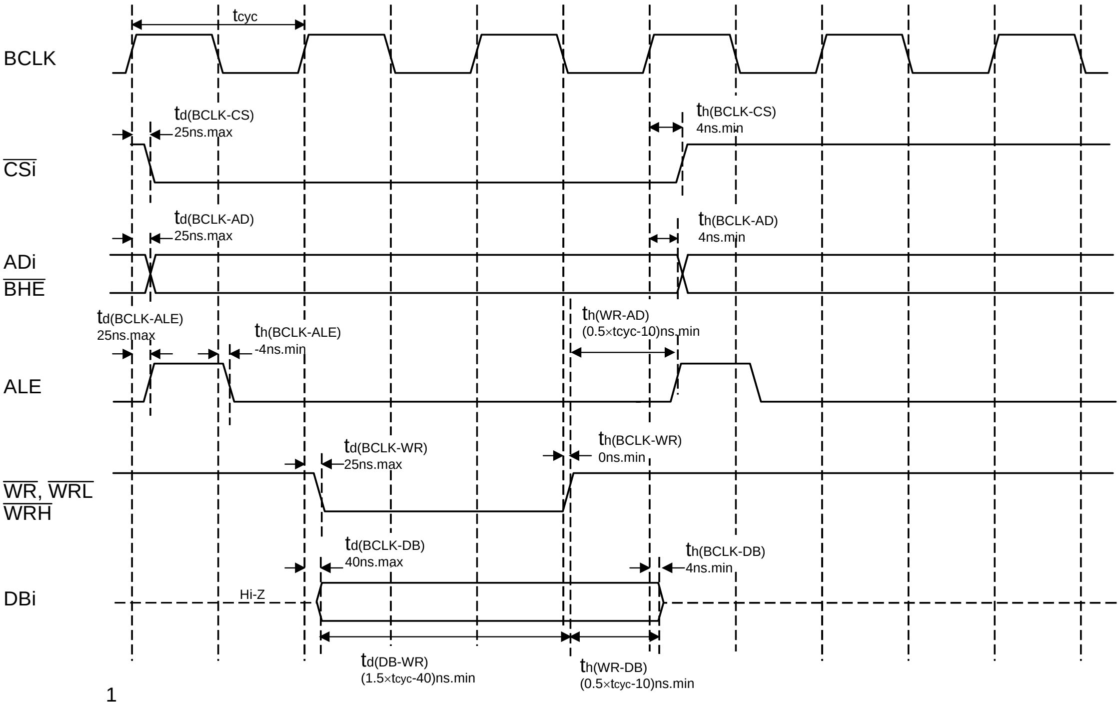
Memory Expansion Mode, Microprocessor Mode

(for 2-wait setting and external area access)

Read timing



Write timing



$T_{cyc}=\frac{1}{f(BCLK)}$

Measuring conditions
- $V_{CC1}=V_{CC2}=5V$
- Input timing voltage : $V_{IL}=0.8V$, $V_{IH}=2.0V$
- Output timing voltage : $V_{OL}=0.4V$, $V_{OH}=2.4V$

Figure 5.8 Timing Diagram (6)

Table 5.31 Electrical Characteristics (2) (1)

Symbol	Parameter		Measuring Condition		Standard			Unit
					Min.	Typ.	Max.	
I_{CC}	Power Supply Current (V_{CC1}=V_{CC2}=2.7V to 3.6V)	In single-chip mode, the output pins are open and other pins are V_{SS}	Mask ROM	f(BCLK)=10MHz No division		8	11	mA
				No division, On-chip oscillation		1		mA
			Flash Memory	f(BCLK)=10MHz, No division		8	13	mA
				No division, On-chip oscillation		1.8		mA
			Flash Memory Program	f(BCLK)=10MHz, VCC1=3.0V		12		mA
			Flash Memory Erase	f(BCLK)=10MHz, VCC1=3.0V		22		mA
			Mask ROM	f(XCIN)=32kHz Low power dissipation mode, ROM (3)		25		µA
			Flash Memory	f(BCLK)=32kHz Low power dissipation mode, RAM (3)		25		µA
				f(BCLK)=32kHz Low power dissipation mode, Flash Memory (3)		420		µA
				On-chip oscillation, Wait mode		45		µA
			Mask ROM Flash Memory	f(BCLK)=32kHz Wait mode (2), Oscillation capability High		6.0		µA
				f(BCLK)=32kHz Wait mode (2), Oscillation capability Low		1.8		µA
				Stop mode Topr =25°C		0.7	3.0	µA
I_{det4}	Low Voltage Detection Dissipation Current (4)					0.6	4	µA
I_{det3}	Reset Area Detection Dissipation Current (4)					0.4	2	µA

NOTES:

1. Referenced to V_{CC1}=V_{CC2}=2.7 to 3.3V, V_{SS} = 0V at T_{opr} = −20 to 85°C / −40 to 85°C, f(BCLK)=10MHz unless otherwise specified.
2. With one timer operated using fC32.
3. This indicates the memory in which the program to be executed exists.
4. I_{det} is dissipation current when the following bit is set to “1” (detection circuit enabled).
   I_{det4}: VC27 bit in the VCR2 register
   I_{det3}: VC26 bit in the VCR2 register

$V_{CC1}=V_{CC2}=3V$

Switching Characteristics
(V_{CC1} = V_{CC2} = 3V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.46 Memory Expansion and Microprocessor Modes (for setting with no wait)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address Output Delay Time	See **Figure 5.12**		30	ns
$t_{h(BCLK-AD)}$	Address Output Hold Time (in relation to BCLK)		4		ns
$t_{h(RD-AD)}$	Address Output Hold Time (in relation to RD)		0		ns
$t_{h(WR-AD)}$	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
$t_{d(BCLK-CS)}$	Chip Select Output Delay Time			30	ns
$t_{h(BCLK-CS)}$	Chip Select Output Hold Time (in relation to BCLK)		4		ns
$t_{d(BCLK-ALE)}$	ALE Signal Output Delay Time			25	ns
$t_{h(BCLK-ALE)}$	ALE Signal Output Hold Time		–4		ns
$t_{d(BCLK-RD)}$	RD Signal Output Delay Time			30	ns
$t_{h(BCLK-RD)}$	RD Signal Output Hold Time		0		ns
$t_{d(BCLK-WR)}$	WR Signal Output Delay Time			30	ns
$t_{h(BCLK-WR)}$	WR Signal Output Hold Time		0		ns
$t_{d(BCLK-DB)}$	Data Output Delay Time (in relation to BCLK)			40	ns
$t_{h(BCLK-DB)}$	Data Output Hold Time (in relation to BCLK) (3)		4		ns
$t_{d(DB-WR)}$	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR) (3)		(NOTE 2)		ns
$t_{d(BCLK-HLDA)}$	HLDA Output Delay Time			40	ns

NOTES:

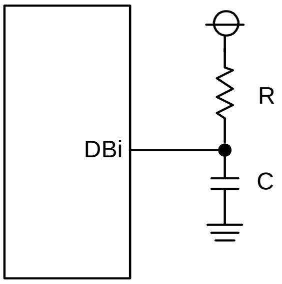
1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 40[ns] \qquad f(BCLK) \text{ is 12.5MHz or less.}$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
   Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
   Hold time of data bus is expressed in
   $t = -CR \text{ X } \ln(1 - V_{OL} / V_{CC2})$
   by a circuit of the right figure.
   For example, when V_{OL} = 0.2V_{CC2}, C = 30pF, R = 1kΩ, hold time of output "L" level is
   $t = -30pF \text{ X } 1k\,\Omega \text{ X } \ln(1 - 0.2V_{CC2} / V_{CC2})$
   $= 6.7ns.$



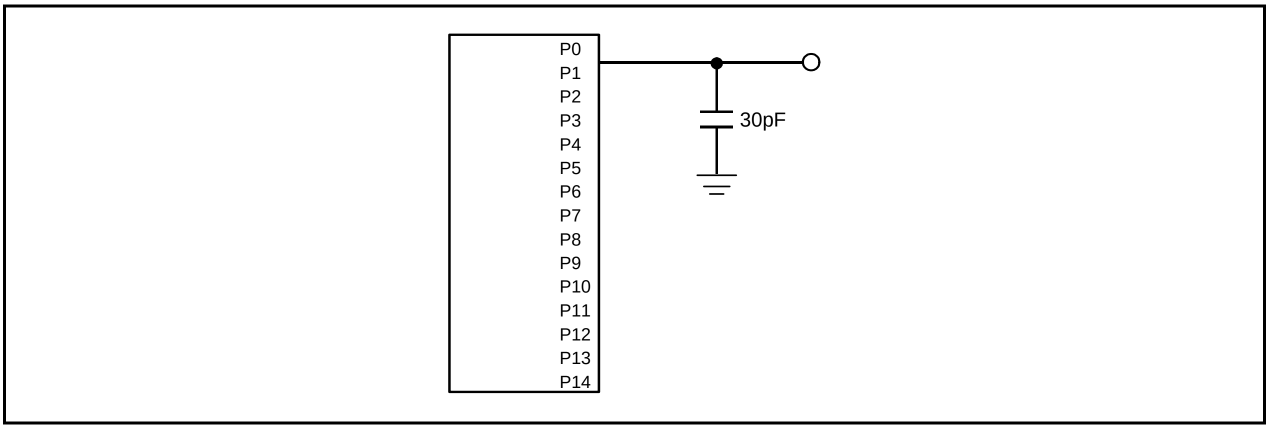
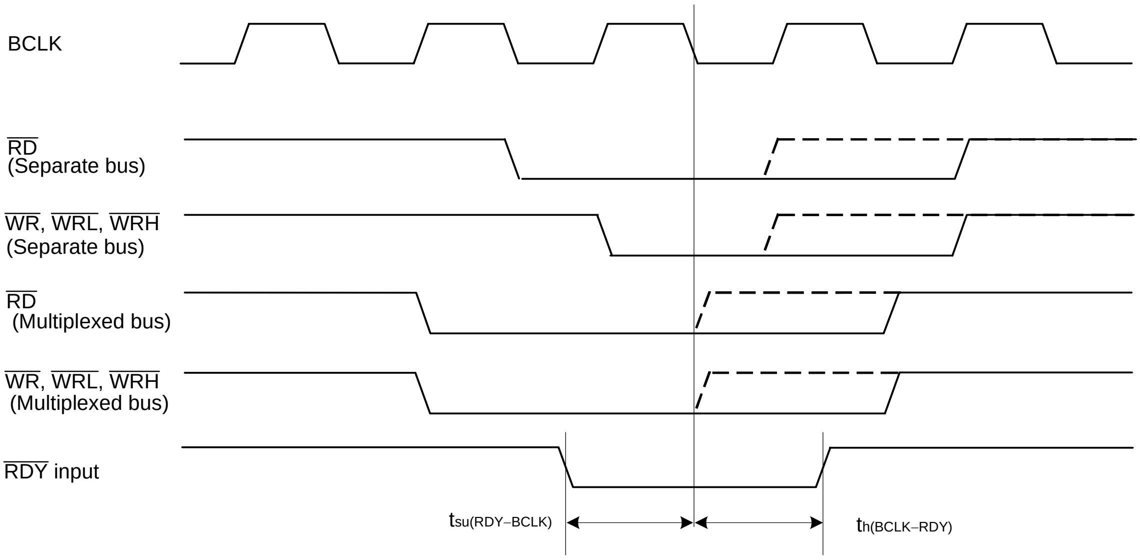


Figure 5.12 Ports P0 to P14 Measurement Circuit

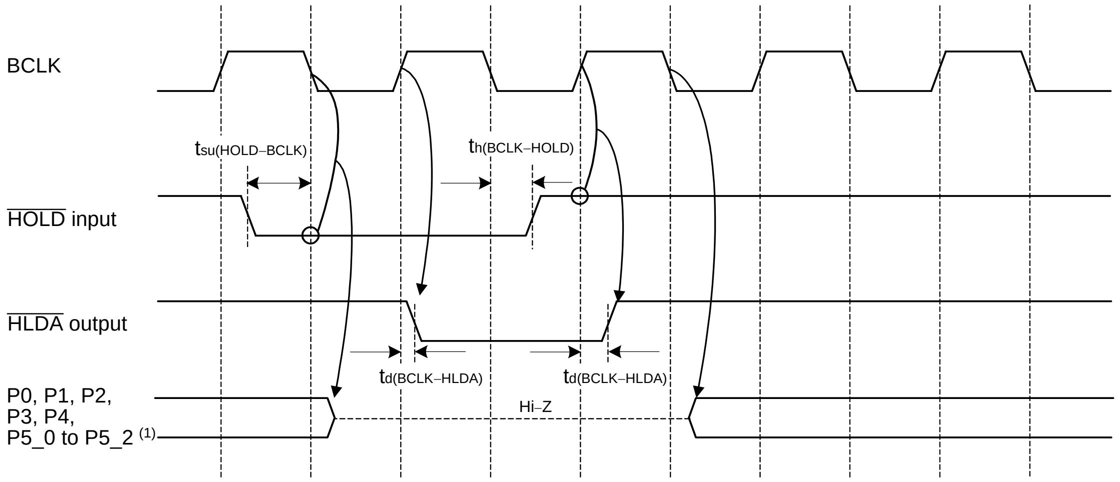
$V_{CC1}=V_{CC2}=3V$

Memory Expansion Mode, Microprocessor Mode

(Effective for setting with wait)



(Common to setting with wait and setting without wait)



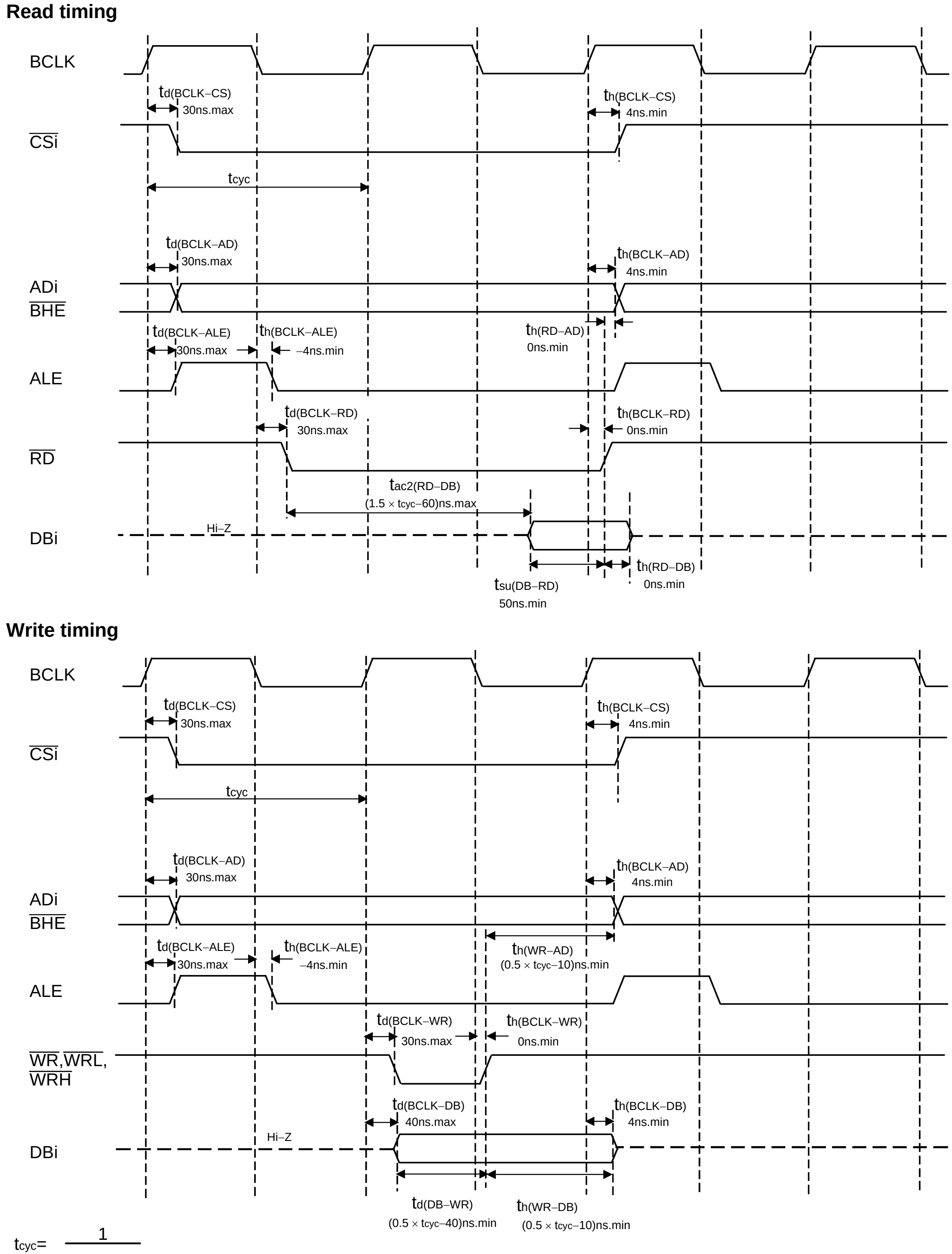
NOTES:
1. These pins are set to high-impedance regardless of the input level of the BYTE pin, PM06 bit in PM0 register and PM11 bit in PM1 register.

Measuring conditions :
· $V_{CC1}=V_{CC2}=3V$
· Input timing voltage : Determined with $V_{IL}=0.6V$, $V_{IH}=2.4V$
· Output timing voltage : Determined with $V_{OL}=1.5V$, $V_{OH}=1.5V$

Figure 5.15 Timing Diagram (3)

Memory Expansion Mode, Microprocessor Mode
(for 1-wait setting and external area access**)**

$V_{CC1}=V_{CC2}=3V$



$$t_{cyc}=\frac{1}{f(BCLK)}$$

Measuring conditions
· $V_{CC1}=V_{CC2}=3V$
· Input timing voltage : $V_{IL}=0.6V$, $V_{IH}=2.4V$
· Output timing voltage : $V_{OL}=1.5V$, $V_{OH}=1.5V$

Figure 5.17 Timing Diagram (5)

Table 5.53 Flash Memory Version Electrical Characteristics (1) for 100 cycle products (B, U)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3)		100			cycle
–	Word Program Time (VCC1=5.0V)			25	200	µs
–	Lock Bit Program Time			25	200	µs
–	Block Erase Time (VCC1=5.0V)	4-Kbyte block	4	0.3	4	s
–		8-Kbyte block		0.3	4	s
–		32-Kbyte block		0.5	4	s
–		64-Kbyte block		0.8	4	s
–	Erase All Unlocked Blocks Time (2)				4×n	s
tPS	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		20			year

Table 5.54 Flash Memory Version Electrical Characteristics (6) for 10,000 cycle products (B7, U7) (Block A and Block 1 (7))

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3, 8, 9)		10,000 (4)			cycle
–	Word Program Time (VCC1=5.0V)			25		µs
–	Lock Bit Program Time			25		µs
–	Block Erase Time (VCC1=5.0V)	4-Kbyte block	4	0.3		s
tPS	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		20			year

NOTES:

1. Referenced to VCC1=4.5 to 5.5V at Topr = 0 to 60 °C unless otherwise specified.
2. n denotes the number of block erases.
3. Program and Erase Endurance refers to the number of times a block erase can be performed. If the program and erase endurance is n (n=100, 1,000, or 10,000), each block can be erased n times. For example, if a 4 Kbytes block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one program and erase endurance. Data cannot be written to the same address more than once without erasing the block. (Rewrite prohibited)
4. Maximum number of E/W cycles for which operation is guaranteed.
5. Ta (ambient temperature)=55 °C. As to the data hold time except Ta=55 °C, please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor.
6. Referenced to VCC1 = 4.5 to 5.5V at Topr = –40 to 85 °C (B7, U7 (T version)) / –40 to 125 °C (B7, U7 (V version)) unless otherwise specified.
7. Table 5.54 applies for block A or block 1 program and erase endurance > 1,000. Otherwise, use Table 5.53.
8. To reduce the number of program and erase endurance when working with systems requiring numerous rewrites, write to unused word addresses within the block instead of rewrite. Erase block only after all possible addresses are used. For example, an 8-word program can be written 256 times maximum before erase becomes necessary. Maintaining an equal number of erasure between block A and block 1 will also improve efficiency. It is important to track the total number of times erasure is used.
9. Should erase error occur during block erase, attempt to execute clear status register command, then block erase command at least three times until erase error disappears.
10. Set the PM17 bit in the PM1 register to “1” (wait state) when executing more than 100 times rewrites (B7 and U7).
11. Customers desiring E/W failure rate information should contact their Renesas technical support representative.

Table 5.55 Flash Memory Version Program/Erase Voltage and Read Operation Voltage Characteristics (at Topr = 0 to 60 °C(B, U), Topr = –40 to 85 °C (B7, U7 (T version)) / –40 to 125 °C (B7, U7 (V version))

Flash Program, Erase Voltage	Flash Read Operation Voltage
VCC1 = 5.0 V ± 0.5 V	VCC1=4.0 to 5.5 V

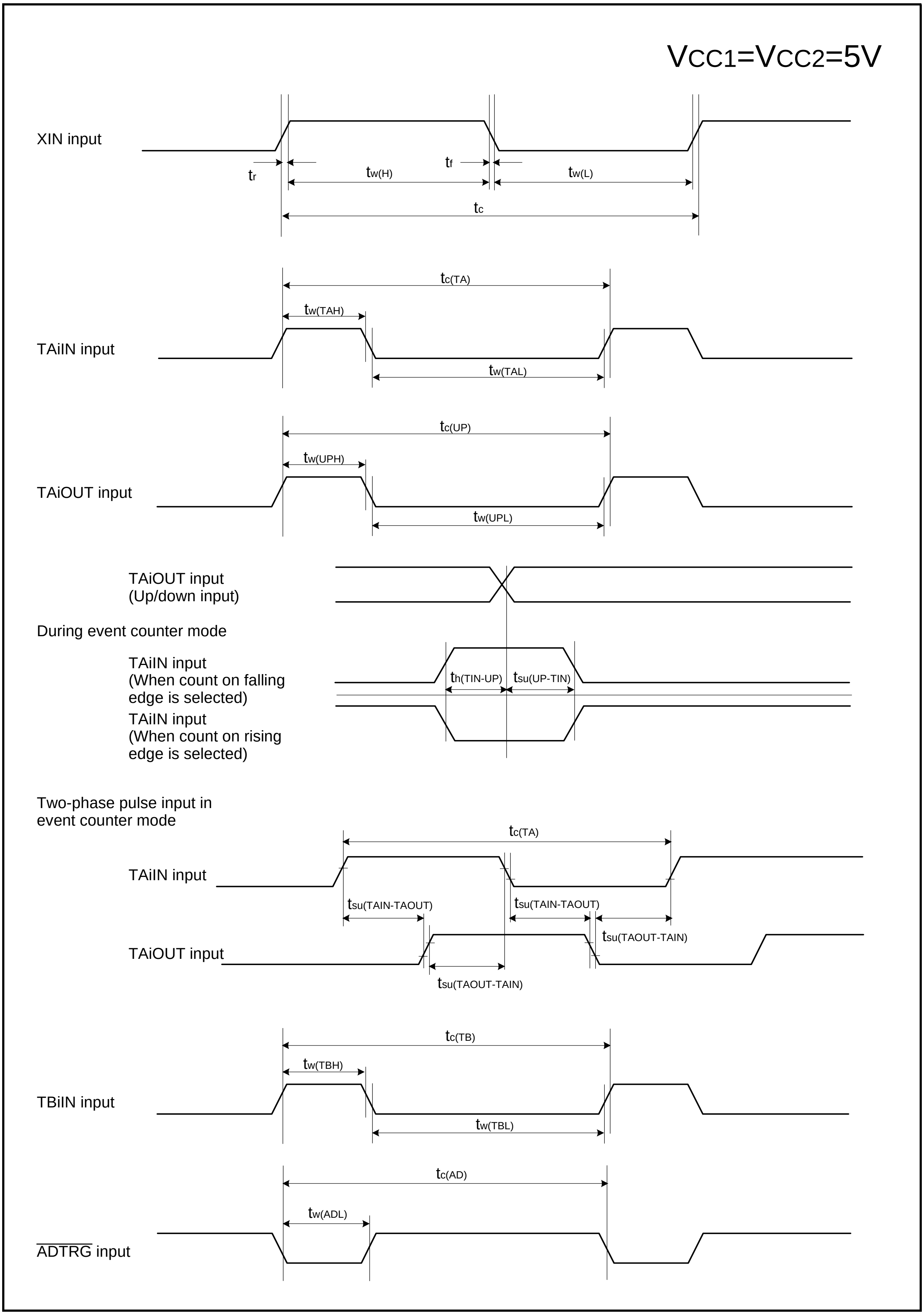


Figure 5.24 Timing Diagram (1)